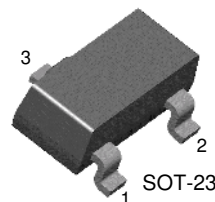


KST5086/5087

Low Noise Transistor



1. Base 2. Emitter 3. Collector

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_a=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------|-----------------------------|-------|------------------|
| V_{CBO} | Collector-Base Voltage | -50 | V |
| V_{CEO} | Collector-Emitter Voltage | -50 | V |
| V_{EBO} | Emitter-Base Voltage | -3 | V |
| I_C | Collector Current | -50 | mA |
| P_C | Collector Power Dissipation | 350 | mW |
| T_{STG} | Storage Temperature | 150 | $^\circ\text{C}$ |

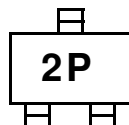
Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Max. | Units |
|---------------|--------------------------------------|---|------|-------|-------|
| BV_{CBO} | Collector-Base Breakdown Voltage | $I_C = -100\mu\text{A}, I_E = 0$ | -50 | | V |
| BV_{CEO} | Collector-Emitter Breakdown Voltage | $I_C = -1\text{mA}, I_B = 0$ | -50 | | V |
| I_{CBO} | Collector Cut-off Current | $V_{CB} = -20\text{V}, I_E = 0$ | | -50 | nA |
| h_{FE} | DC Current Gain | | | | |
| | : KST5086 | $V_{CE} = -5\text{V}, I_C = -100\mu\text{A}$ | 150 | 500 | |
| | : KST5087 | | 250 | 800 | |
| | : KST5086 | $V_{CE} = -5\text{V}, I_C = -1\text{mA}$ | 150 | | |
| | : KST5087 | | 250 | | |
| | : KST5086 | $V_{CE} = -5\text{V}, I_C = -10\text{mA}$ | 150 | | |
| | : KST5087 | | 250 | | |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = -10\text{mA}, I_B = -1\text{mA}$ | | -0.3 | V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage | $I_C = -10\text{mA}, I_B = -1\text{mA}$ | | -0.85 | V |
| f_T | Current Gain Bandwidth Product | $V_{CE} = -5\text{V}, I_C = -500\mu\text{A}$ $f = 20\text{MHz}$ | 40 | | MHz |
| C_{ob} | Output Capacitance | $V_{CB} = -5\text{V}, I_E = 0$ $f = 100\text{MHz}$ | | 4 | pF |
| NF | Noise Figure | | | | |
| | : KST5086 | $I_C = -100\mu\text{A}, V_{CE} = -5\text{V}$ $R_S = 3\text{K}\Omega, f = 1\text{KHz}$ | | 3 | dB |
| | : KST5087 | | | 2 | dB |
| | : KST5087 | $V_{CE} = -5\text{V}, I_C = -20\text{mA}$ $R_S = 10\text{K}\Omega, f = 10\text{Hz to } 15.7\text{KHz}$ | | 2 | dB |

Marking Code

| Type | KST5086 | KST5087 |
|------|---------|---------|
| Mark | 2P | 2Q |

Marking



Typical Characteristics

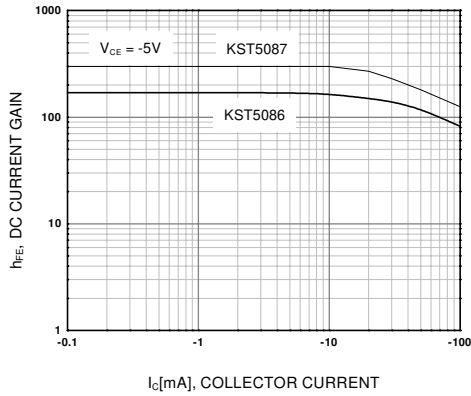


Figure 1. DC current Gain

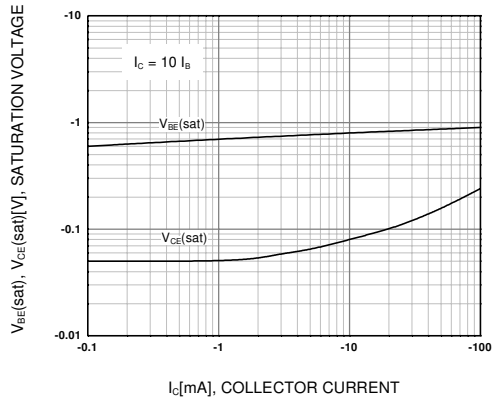


Figure 2. Base-Emitter Saturation Voltage
Collector-Emmitter Saturation Voltage

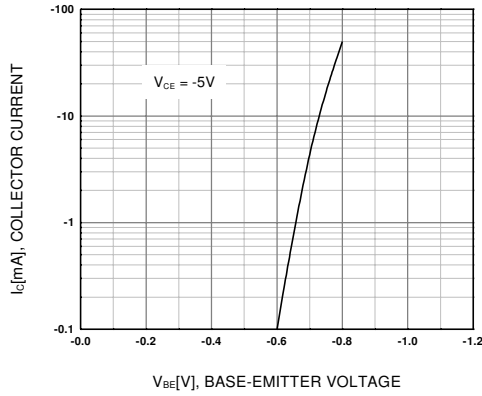


Figure 3. Base-Emitter On Voltage

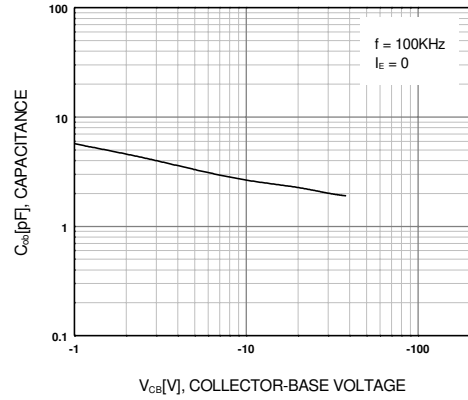


Figure 4. Output Capacitance

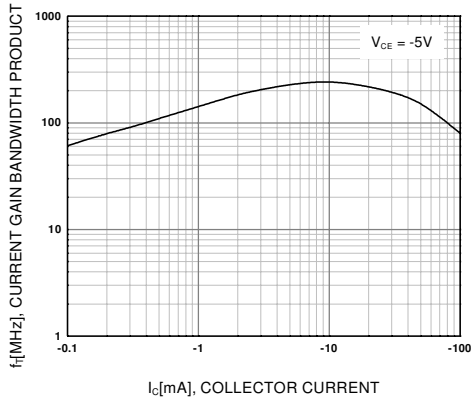
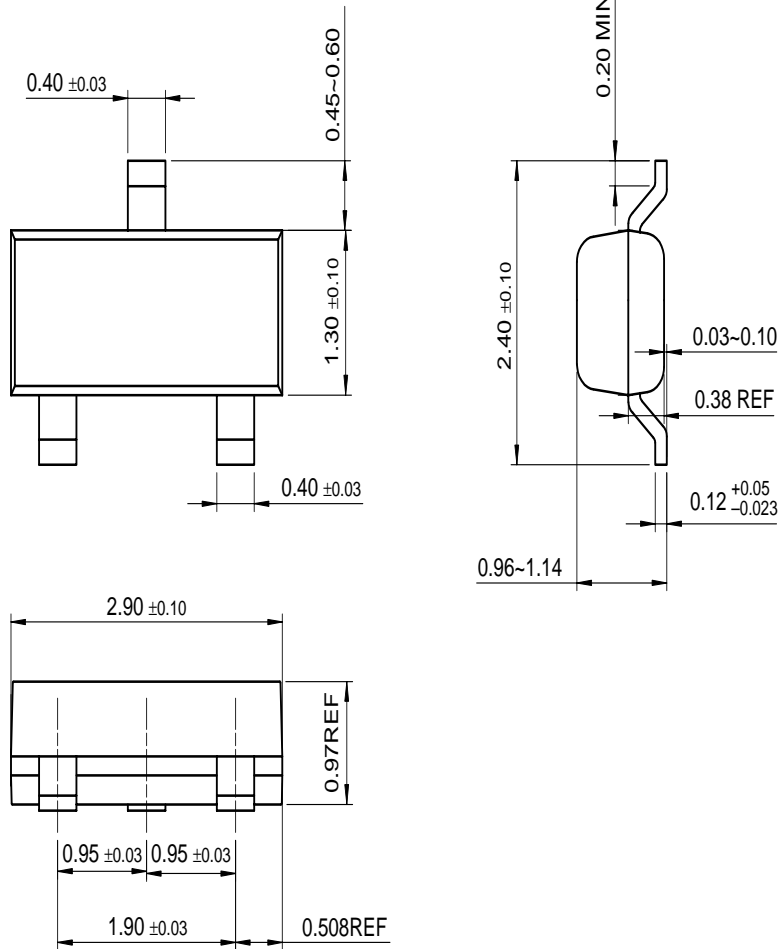


Figure 5. Current Gain Bandwidth Product

Package Dimensions

SOT-23

KST5086/5087



Dimensions in Millimeters

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| | | | | |
|---|----------------------------------|---------------------------------|----------------------------------|------------------------------|
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| ActiveArray TM | FACT Quiet series TM | ISOPLANAR TM | POP TM | Stealth TM |
| Bottomless TM | FAST [®] | LittleFET TM | Power247 TM | SuperSOT TM -3 |
| CoolFET TM | FAST ^r TM | MicroFET TM | PowerTrench [®] | SuperSOT TM -6 |
| CROSSVOL TM | FRFET TM | MicroPak TM | QFET TM | SuperSOT TM -8 |
| DOME TM | GlobalOptoisolator TM | MICROWIRE TM | QS TM | SyncFET TM |
| EcoSPARK TM | GTO TM | MSX TM | QT Optoelectronics TM | TinyLogic TM |
| E ² CMOS TM | HiSeC TM | MSXPro TM | Quiet Series TM | TruTranslation TM |
| EnSigna TM | I ² C TM | OCX TM | RapidConfigure TM | UHC TM |
| Across the board. Around the world. TM | | OCXPro TM | RapidConnect TM | UltraFET [®] |
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PRODUCT STATUS DEFINITIONS

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|--------------------------|------------------------|---|
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